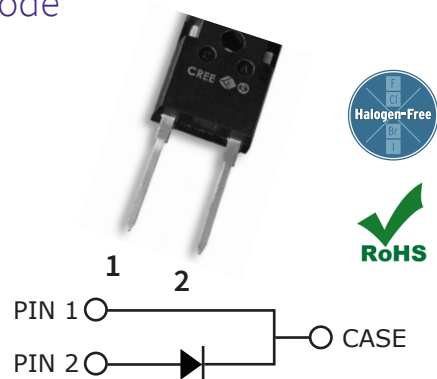


C4D30120H

4th Generation 1200 V, 30 A Silicon Carbide Schottky Diode

Description

With the performance advantages of a Silicon Carbide (SiC) Schottky Barrier diode, power electronics systems can expect to meet higher efficiency standards than Si-based solutions, while also reaching higher frequencies and power densities. SiC diodes can be easily paralleled to meet various application demands, without concern of thermal runaway. In combination with the reduced cooling requirements and improved thermal performance of SiC products, SiC diodes are able to provide lower overall system costs in a variety of diverse applications.



Package Type: TO-247-2
Marking: C4D30120

Features

- Low Forward Voltage (V_f) Drop with Positive Temperature Coefficient
- Zero Reverse Recovery Current / Forward Recovery Voltage
- Temperature-Independent Switching Behavior
- Increased Creepage / Clearance + HV-H3TRB Rugged

Applications

- Battery Chargers
- Solar & Renewable Energy Power Conversion
- Industrial Power Supplies
- Boost Diodes in PFC & DC-DC

Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit	Test Conditions	Note
Repetitive Peak Reverse Voltage	V_{RRM}	1200	V		
DC Blocking Voltage	V_{DC}	1200			
Continuous Forward Current	I_F	94	A	$T_J = 25^\circ\text{C}$	Fig. 3
		45		$T_J = 135^\circ\text{C}$	
		30		$T_J = 155^\circ\text{C}$	
Repetitive Peak Forward Surge Current	I_{FRM}	121	A	$T_c = 25^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Pulse}$	
		68		$T_c = 110^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Pulse}$	
Non-Repetitive Forward Surge Current	I_{FSM}	233	A	$T_c = 25^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Pulse}$	
		209		$T_c = 110^\circ\text{C}, t_p = 10\text{ ms}, \text{Half Sine Pulse}$	
Power Dissipation	P_{tot}	441	W	$T_J = 25^\circ\text{C}$	Fig. 4
		191		$T_J = 110^\circ\text{C}$	
i^2t Value	$\int i^2t$	271	A^2s	$T_c = 25^\circ\text{C}, t_p = 10\text{ ms}$	
		218		$T_c = 110^\circ\text{C}, t_p = 10\text{ ms}$	



Electrical Characteristics

Parameter	Symbol	Typ.	Max.	Units	Test Conditions	Note
Forward Voltage	V_F	1.5	1.8	V	$I_F = 30 \text{ A}, T_J = 25 \text{ }^\circ\text{C}$	Fig. 1
		2.2	3		$I_F = 30 \text{ A}, T_J = 175 \text{ }^\circ\text{C}$	
Reverse Current	I_R	40	250	μA	$V_R = 1200 \text{ V}, T_J = 25 \text{ }^\circ\text{C}$	Fig. 2
		70	450		$V_R = 1200 \text{ V}, T_J = 175 \text{ }^\circ\text{C}$	
Total Capacitive Charge	Q_C	152		nC	$V_R = 800 \text{ V}, T_J = 25 \text{ }^\circ\text{C}$	Fig. 5
Total Capacitance	C	2,177		pF	$V_R = 0 \text{ V}, T_J = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$	Fig. 6
		136			$V_R = 400 \text{ V}, T_J = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$	
		100			$V_R = 800 \text{ V}, T_J = 25 \text{ }^\circ\text{C}, f = 1 \text{ MHz}$	
Capacitance Stored Energy	E_C	44		μJ	$V_R = 800 \text{ V}$	Fig. 7

Note:

SiC Schottky Diodes are majority carrier devices, so there is no reverse recovery charge.

Thermal & Mechanical Characteristics

Parameter	Symbol	Value	Units	Note
Thermal Resistance, Junction to Case (Typ.)	$R_{\theta,JC}$	0.34	$^\circ\text{C} / \text{W}$	
Operating Junction & Storage Temperature	T_J, T_{stg}	-55 to +175	$^\circ\text{C}$	Fig. 8
Maximum Processing Temperature	T_{PROC}	325		10 min. Maximum

Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Value
Human Body Model	HBM	Class 3B ($\geq 8000 \text{ V}$)
Charge Device Model	CDM	Class C3 ($\geq 1000 \text{ V}$)



Typical Performance

Figure 1. Forward Characteristics

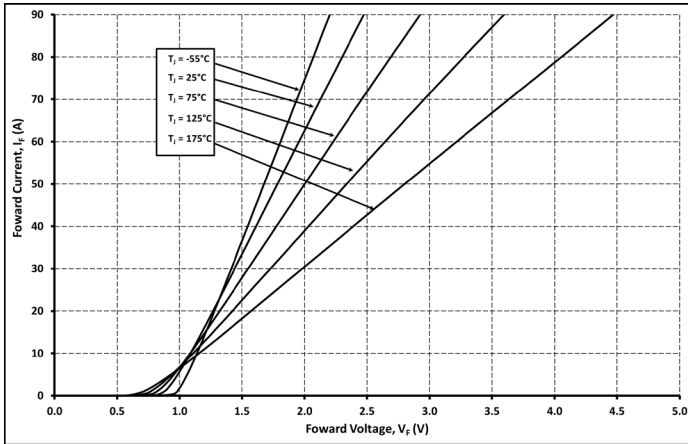


Figure 2. Reverse Characteristics

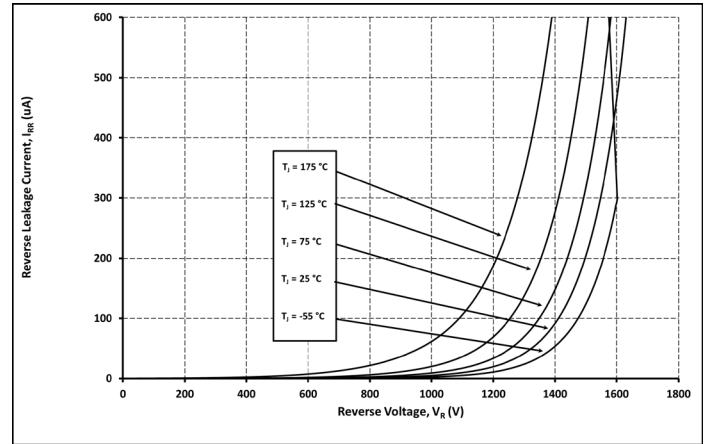


Figure 3. Current Derating

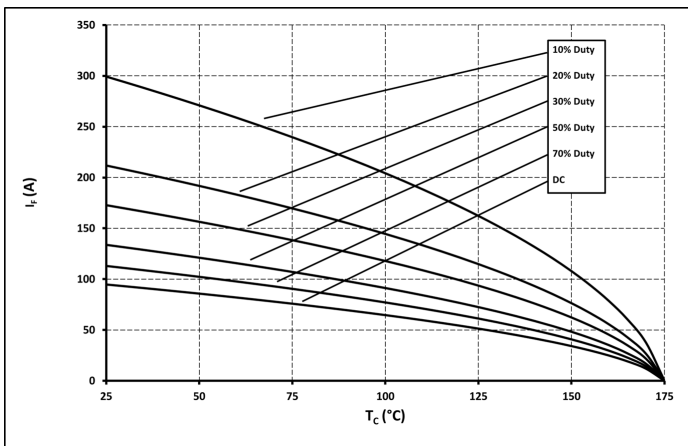


Figure 4. Power Derating

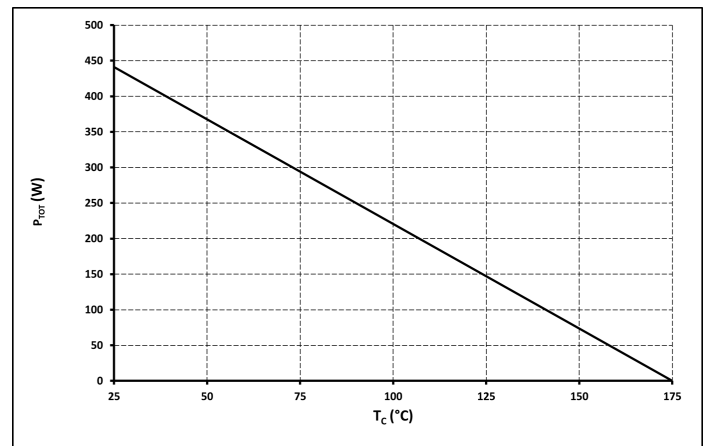


Figure 5. Total Capacitance Charge vs. Reverse Voltage

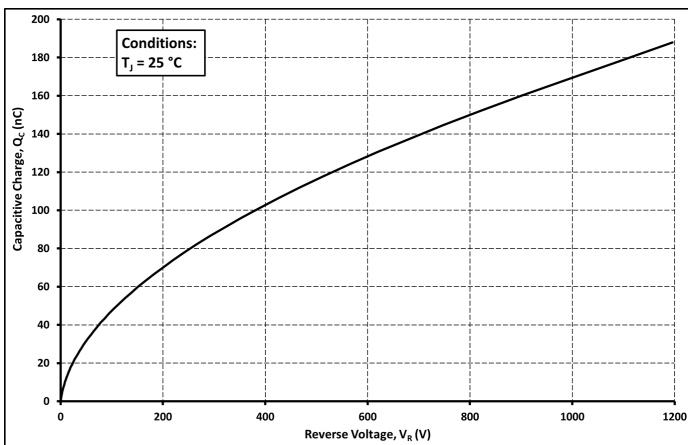
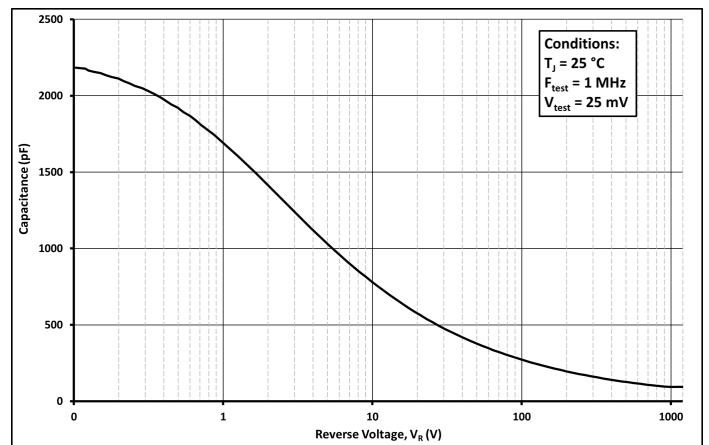


Figure 6. Capacitance vs. Reverse Voltage





Typical Performance

Figure 7. Capacitance Stored Energy

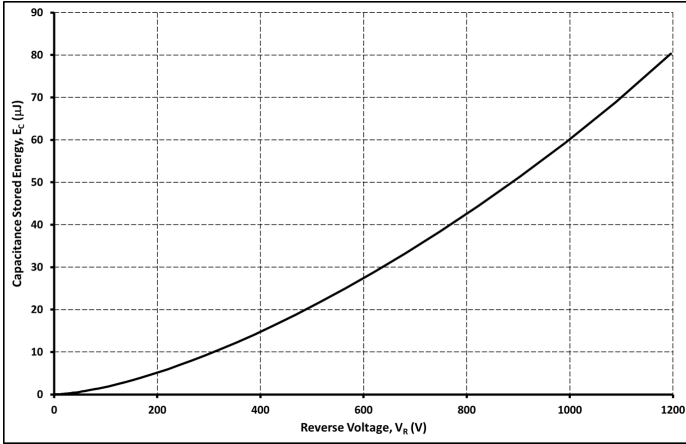


Figure 8. Transient Thermal Impedance

